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What is claimed is:

1. A semiconductor switch comprising:
 - a first electrode, a second electrode, and a third electrode formed on a semiconductor substrate;
- 5 said first electrode and said second electrode connected with the earth and are disposed in parallel to each other,
 - said third electrode formed between said source first and said second electrode;
- 10 a first terminal coupled to one end of said third electrode; and
- a second terminal coupled to the other end of said third electrode.

2. The switch is claimed in claim 1, wherein said first electrode is a drain electrode of a transistor, said second electrode is a source electrode of said transistor, said third electrode is a gate electrode of said transistor.

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3. The switch is claimed in claim 1, wherein said first electrode is a first cathode electrode of a diode, said second electrode is a second cathode electrode of said diode, said third electrode is an anode electrode of said diode.

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4. The switch is claimed in claim 1, wherein said first electrode is a first anode electrode of a diode, said second electrode is a second anode electrode of said diode, said third electrode is a cathode electrode of said diode.

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5. A switching circuit comprising:

a coplanar transmission line having a signal line, conductors arranged such that said signal line is sandwiched between the conductors, said conductors applied 5 to ground potential;

an element having a first electrode coupled to said coplanar transmission line, a second electrode, a third electrode, said second and third electrodes applied to ground potential; and

10 a signal terminal coupled to said coplanar transmission line.

6. The switching circuit is claimed in claim 5, wherein said first electrode is a drain electrode of a transistor, 15 said second electrode is a source electrode of said transistor, said third electrode is a gate electrode of said transistor.

7. The switching circuit is claimed in claim 5, wherein said first electrode is a first cathode electrode of a diode, said second electrode is a second cathode electrode of said diode, said third electrode is an anode electrode of said 5 diode.

8. The switching circuit is claimed in claim 5, wherein said first electrode is a first anode electrode of a diode, said second electrode is a second anode electrode of said

10 diode, said third electrode is a cathode electrode of said diode.

9. The switching circuit as claimed in claim 5, wherein said first, second, and third electrode are formed on a substrate including an AlGaAs layer and an InGaAs layer.

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